



Mechanical Data	Notes
Dice size	Ax:600um,Bx:420um/P1,3,4,6-85*95um/Pin 5-270*105um
Wafer size	4" (Gross die:27,500pcs/Good die>25,575pcs)
Chip Thickness	(A)138um±12um (B)470um±20um
Scribe line width	60um
Top metal	Al/Au/Ag
Back side metal	Al/Au/Ag/Sn

Parameter	Symbol	Conditions	Value	Unit
Reverse stand-off voltage	V_{RWM}		5.0	V
Peak pulse power	PPP	$T_p=8/20\mu s$	150**	W
Peak pulse current	IPP	$T_p=8/20\mu s$	5.0**	A
Electrostatic discharge	VESD	IEC61000-4-2 Level 4	± 15(AIR)	KV
Max.junction temp.	T_j		+150	°C

Characteristics $T_A=25^\circ C$

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Breakdown voltage	V_{BR}	$I_T=1mA$ Pin 5 to 2	6.1	8.0	8.5	V
Reverse leakage current	I_R	$V_R=5V$ Pin 1,3,4,5,6 to 2			0.9	μA
Forward Voltage	V_F	$I_F=15mA$ Pin2 to Pin1,3,4,5,6			0.95	V
Clamping Voltage	V_C	$I_{PP}=1A$ $I_{PP}=5A$			15.0 28.0	V
Diode capacitance I/O-GND	$C_{I/O-GND}$	$V_R=0V$ $f=1MHz$			0.8	pf
Diode capacitance I/O-I/O	$C_{I/O-I/O}$	$V_R=0V$ $f=1MHz$			0.4	pf

Notes:

- (1)sampling testing:no bad dice inking/guaranteed good die >93%
- (2)Testing follow customer
- (3) $T_j=T_a+R_{th(j-a)}*(p_f+p_r)$, where $R_{th(j-a)}$ -thermal resistance, P_f -forward power dissipation,
 P_r -revers power dissipation
- (4)**For device testing